

## DATASHEET PNP SILICON TRANSISTOR

### 主要用途

音频功率放大。

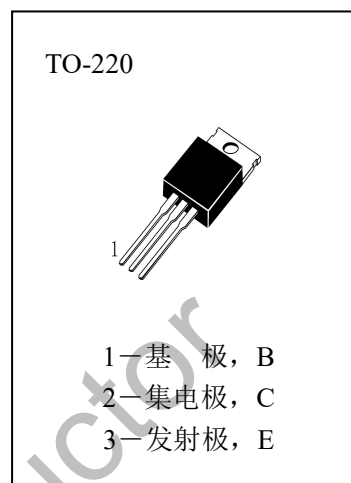
### 极限值 (T<sub>a</sub>=25℃)

T <sub>stg</sub>	贮存温度	-55~150℃
T <sub>j</sub>	结温	150℃
P <sub>C</sub>	集电极功率耗散 (T <sub>c</sub> =25℃)	65W
P <sub>C</sub>	集电极功率耗散 (T <sub>A</sub> =25℃)	2W
V <sub>CB0</sub>	集电极-基极电压	-100V
V <sub>CE0</sub>	集电极-发射极电压	-100V
V <sub>EB0</sub>	发射极-基极电压	-5V
I <sub>C</sub>	集电极电流	-6A
I <sub>B</sub>	基极电流	-2A

### 电参数 (T<sub>a</sub>=25℃)

参数符号	符号说明	最小值	典型值	最大值	单位	测试条件
I <sub>CE0</sub>	集电极-发射极截止电流			-0.7	mA	V <sub>CE</sub> =-60V, I <sub>B</sub> =0
I <sub>EB0</sub>	集电极-基极截止电流			-1	mA	V <sub>EB</sub> =-5V, I <sub>C</sub> =0
I <sub>CES</sub>	集电极-发射极饱和电流			-400	μA	V <sub>CE</sub> =-100V, V <sub>EB</sub> =0
HFE(1)	直流电流增益	30				V <sub>CE</sub> =-4V, I <sub>C</sub> =-0.3A
HFE(2)	直流电流增益	15		100		V <sub>CE</sub> =-4V, I <sub>C</sub> =-3A
V <sub>CE(sat)</sub>	集电极-发射极饱和压降			-1.5	V	I <sub>C</sub> =-6A, I <sub>B</sub> =-600mA
V <sub>BE(on)</sub>	基极-发射极导通电压			-2.0	V	V <sub>CE</sub> =-4V, I <sub>C</sub> =-6A
BV <sub>CE0</sub>	集电极-发射极击穿电压	-100			V	I <sub>C</sub> =-30mA, I <sub>B</sub> =0
f <sub>T</sub>	特征频率	3.0			MHz	V <sub>CE</sub> =-10V, I <sub>C</sub> =-500mA f=1MHz

### 外形图及引脚排列



### HFE (2) 分档

## DATASHEETL

### PNP SILICON TRANSISTOR

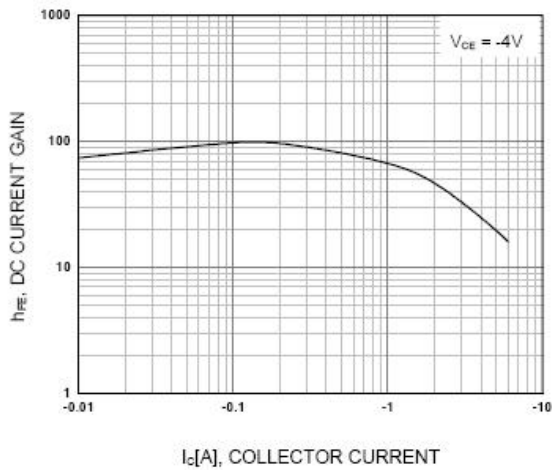


Figure 1. DC current Gain

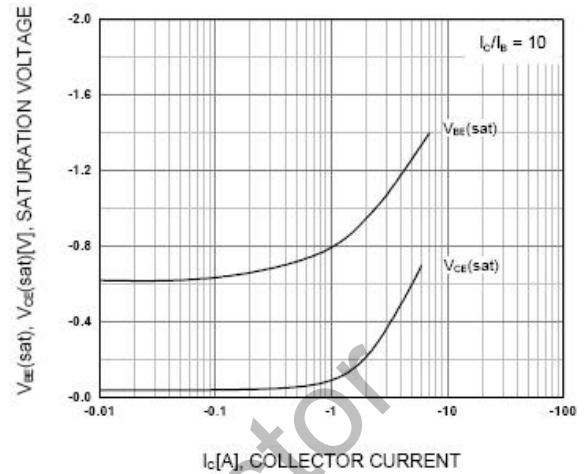


Figure 2. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

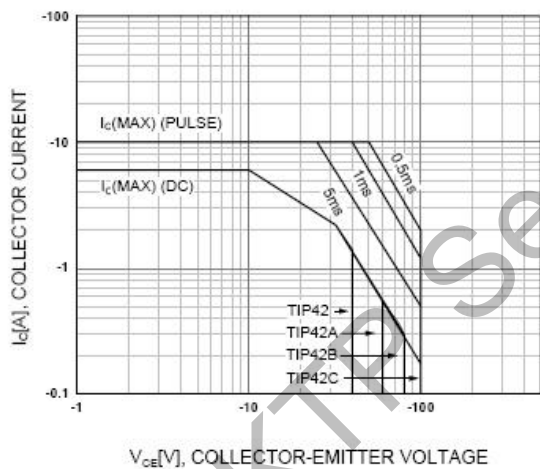


Figure 3. Safe Operating Area

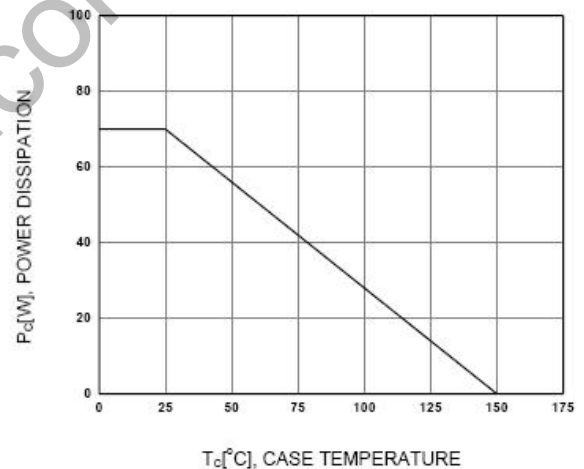


Figure 4. Power derating